forming a gate insulating film in contact with the semiconductor film from the surface of which the contaminating impurity has been removed.

15. (Amended) A method of manufacturing a semiconductor device, comprising steps of:

forming at least one semiconductor island over a substrate;

spinning the substrate;

contacting an etching solution to a surface of said semiconductor island and scattering the etching solution during said spinning, thereby contaminating impurities are removed from the surface; and then

forming a gate insulating film over said semiconductor island.

19. (Amended) A method of manufacturing a semiconductor device, comprising steps of:

forming a semiconductor film over a substrate;

crystallizing said semiconductor film;

forming at least one semiconductor island over said substrate by patterning the crystallized semiconductor film ;

spinning the substrate;

contacting an etching solution to a surface of said semiconductor island and scattering the etching solution during said spinning, thereby contaminating impurities are removed from the surface; and then

forming a gate insulating film over said semiconductor island; and

forming a gate electrode over said gate insulating film.

23. (Amended) A method of manufacturing a semiconductor device, comprising steps of:

forming gate wirings over a substrate;

spinning the substrate;

C4 contacting an etching solution to surfaces of said substrate and said gate wirings and scattering the etching solution during said spinning, thereby contaminating impurities are removed from the surfaces; and then

forming a gate insulating film and a semiconductor film over said gate wirings.

27. (Amended) A method of manufacturing a semiconductor device, comprising steps of:

forming gate wirings over a substrate;

spinning the substrate;

C5 contacting an etching solution to surfaces of said substrate and said gate wirings and scattering the etching solution during said spinning, thereby contaminating impurities are removed from the surfaces; and then

forming a gate insulating film and a semiconductor film over said gate wirings, continuously.